

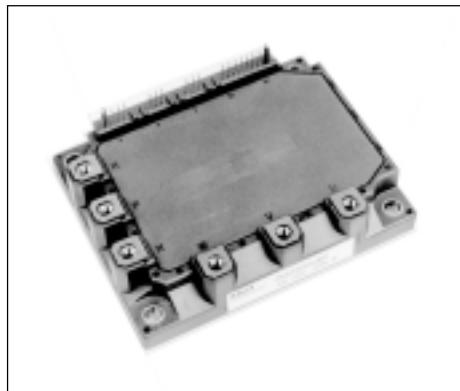
7MBP50RA120

IGBT-IPM R series

1200V / 50A 7 in one-package

■ Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- Compatible with existing IPM-N series packages
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



■ Maximum ratings and characteristics

- Absolute maximum ratings(at $T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Rating		Unit
		Min.	Max.	
DC bus voltage	V _{DC}	0	900	V
DC bus voltage (surge)	V _{DC(surge)}	0	1000	V
DC bus voltage (short operating)	V _{SC}	200	800	V
Collector-Emitter voltage	V _{CES}	0	1200	V
DB Reverse voltage	V _R	-	1200	V
INV	Collector current DC	I _C	-	50 A
	1ms	I _{CP}	-	100 A
	DC	-I _C	-	50 A
DB	Collector power dissipation One transistor	P _C	-	357 W
	Collector current DC	I _C	-	25 A
	1ms	I _{CP}	-	50 A
	Forward current of Diode	I _F	-	25 A
	Collector power dissipation One transistor	P _C	-	198 W
Junction temperature	T _j	-	150	°C
Input voltage of power supply for Pre-Driver	V _{CC} *1	0	20	V
Input signal voltage	V _{IN} *2	0	V _Z	V
Input signal current	I _{IN}	-	1	mA
Alarm signal voltage	V _{ALM} *3	0	V _{CC}	V
Alarm signal current	I _{ALM} *4	-	15	mA
Storage temperature	T _{STG}	-40	125	°C
Operating case temperature	T _{OP}	-20	100	°C
Isolating voltage (Case-Terminal)	V _{ISO} *5	-	AC2.5	kV
Screw torque	Mounting (M5)	-	3.5 *6	N·m
	Terminal (M5)	-	3.5 *6	N·m

*1 Apply V_{CC} between terminal No. 3 and 1, 6 and 4, 9 and 7, 11 and 10.

*2 Apply V_{IN} between terminal No. 2 and 1, 5 and 4, 8 and 7, 12,13,14,15 and 10.

*3 Apply V_{ALM} between terminal No. 16 and 10.

*4 Apply I_{ALM} to terminal No. 16.

*5 50Hz/60Hz sine wave 1 minute.

*6 Recommendable Value : 2.5 to 3.0 N·m

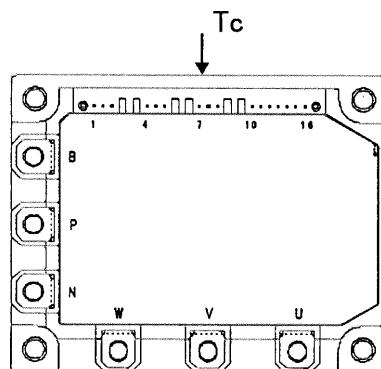


Fig.1 Measurement of case temperature

● Electrical characteristics of power circuit (at $T_c=T_j=25^\circ\text{C}$, $V_{CC}=15\text{V}$)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
INV	I _{CES}	V _{CE} =1200V input terminal open	-	-	1.0	mA
	V _{CE(sat)}	I _C =50A	-	-	2.6	V
	V _F	-I _C =50A	-	-	3.0	V
DB	I _{CES}	V _{CE} =1200V input terminal open	-	-	1.0	mA
	V _{CE(sat)}	I _C =25A	-	-	2.6	V
	V _F	-I _C =25A	-	-	3.3	V

● Electrical characteristics of control circuit(at $T_c=T_j=25^\circ C$, $V_{cc}=15V$)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Power supply current of P-line side Pre-driver(one unit)	I_{ccp}	$f_{sw}=0$ to $15kHz$ $T_c=-20$ to $100^\circ C$ *7	3	-	18	mA
Power supply current of N-line side three Pre-driver	I_{ccn}	$f_{sw}=0$ to $15kHz$ $T_c=-20$ to $100^\circ C$ *7	10	-	65	mA
Input signal threshold voltage (on/off)	$V_{in(th)}$	ON	1.00	1.35	1.70	V
		OFF	1.25	1.60	1.95	V
Input zener voltage	V_z	$R_{in}=20k\ ohm$	-	8.0	-	V
Over heating protection temperature level	T_{COH}	$V_{DC}=0V$, $I_c=0A$, Case temperature Fig.1	110	-	125	°C
Hysteresis	T_{CH}		-	20	-	°C
IGBT chips over heating protection temperature level	T_{jOH}	surface of IGBT chips	150	-	-	°C
Hysteresis	T_{jH}		-	20	-	°C
Collector current protection level	INV	I_{oc} $T_j=125^\circ C$	75	-	-	A
	DB	I_{oc} $T_j=125^\circ C$	38	-	-	A
Over current protection delay time	t_{DOC}	$T_j=25^\circ C$ Fig.2	-	10	-	μs
Under voltage protection level	V_{UV}		11.0	-	12.5	V
Hysteresis	V_H		0.2	-	-	V
Alarm signal hold time	t_{ALM}		1.5	2	-	ms
SC protection delay time	t_{SC}	$T_j=25^\circ C$ Fig.3	-	-	12	μs
Limiting resistor for alarm	R_{ALM}		1425	1500	1575	ohm

*7 Switching frequency of IPM

● Dynamic characteristics(at $T_c=T_j=125^\circ C$, $V_{cc}=15V$)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Switching time (IGBT)	t_{on}	$I_c=50A$, $V_{DC}=600V$	0.3	-	-	μs
	t_{off}		-	-	3.6	μs
Switching time (FWD)	t_{trr}	$I_F=50A$, $V_{DC}=600V$	-	-	0.4	μs

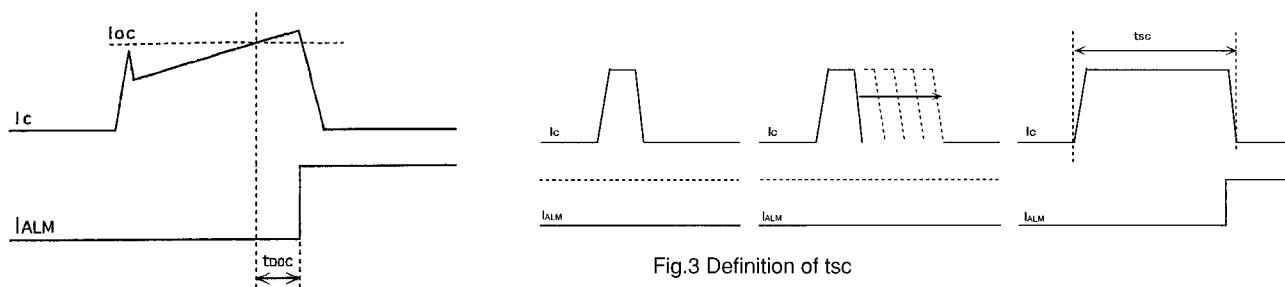


Fig.2 Definition of OC delay time

Fig.3 Definition of tsc

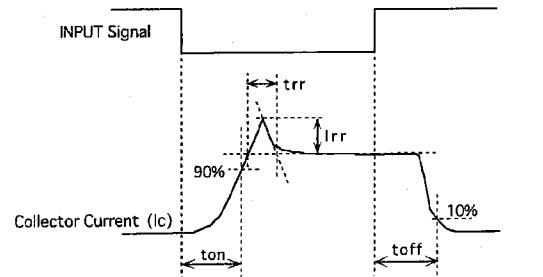


Fig.4 Definition of switching time

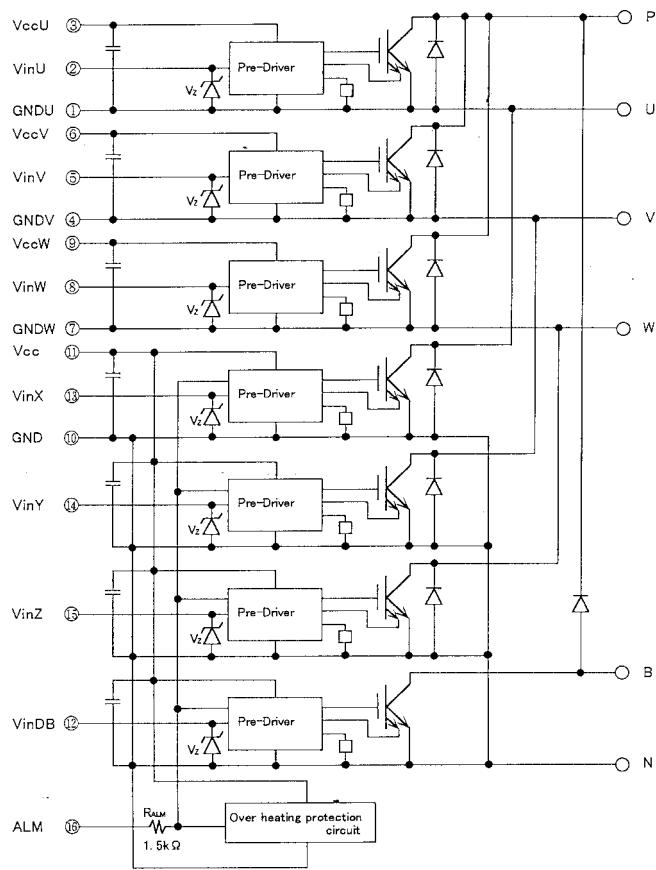
● Thermal characteristics($T_c=25^\circ C$)

Item	Symbol	Typ.	Max.	Unit
Junction to Case thermal resistance	INV IGBT	$R_{th(j-c)}$	-	0.35 °C/W
	FWD	$R_{th(j-c)}$	-	0.85 °C/W
	DB IGBT	$R_{th(j-c)}$	-	0.63 °C/W
Case to fin thermal resistance with compound	$R_{th(c-f)}$		0.05	- °C/W

● Recommendable value

Item	Symbol	Min.	Typ.	Max.	Unit
DC bus voltage	V_{DC}	200	-	800	V
Operating power supply voltage range of Pre-driver	V_{cc}	13.5	15	16.5	V
Switching frequency of IPM	f_{sw}	1	-	20	kHz
Screw torque	Mounting (M5)	-	2.5	-	N·m
	Terminal (M5)	-	2.5	-	N·m

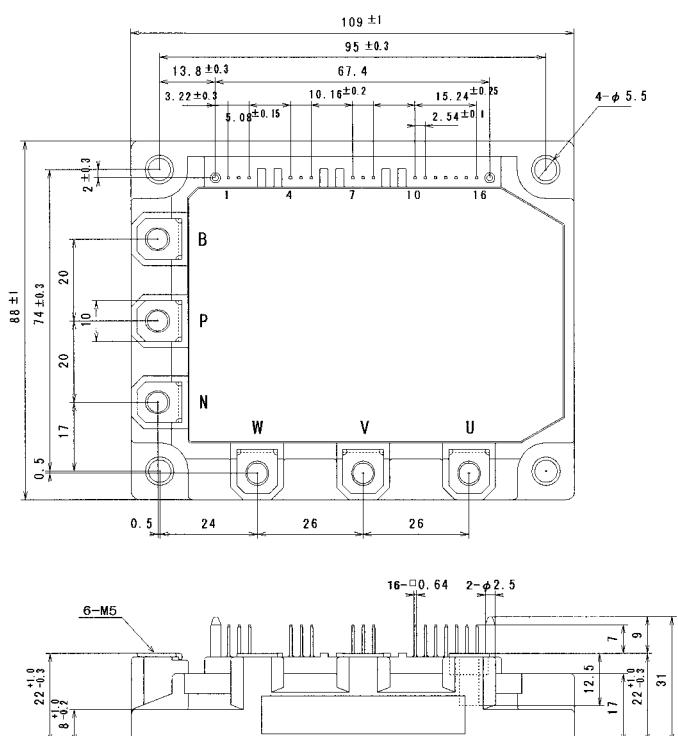
■ Block diagram



Pre-drivers include following functions

- Amplifier for driver
- Short circuit protection
- Undervoltage lockout circuit
- Over current protection
- IGBT chip over heating protection

■ Outline drawings, mm



Mass : 440g